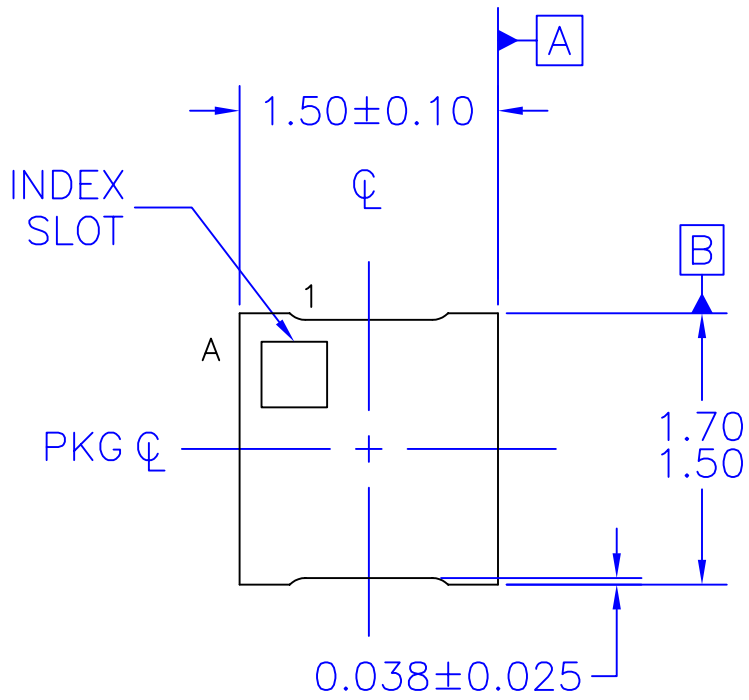
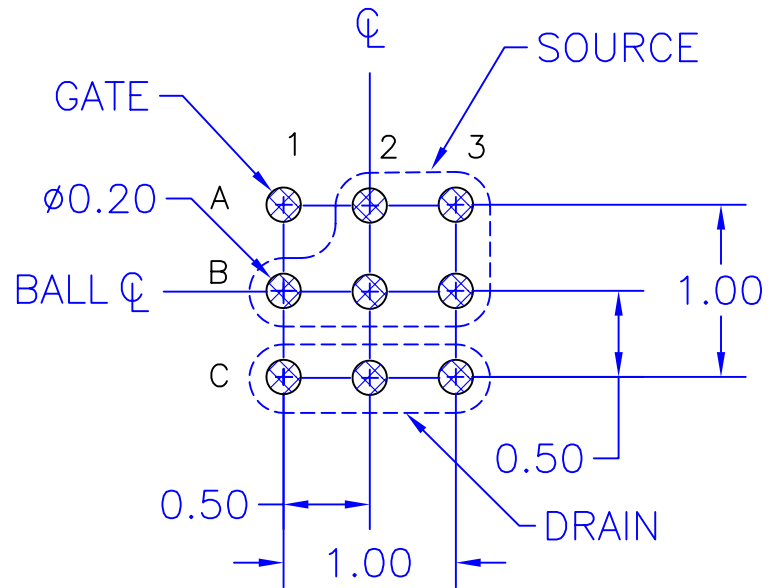


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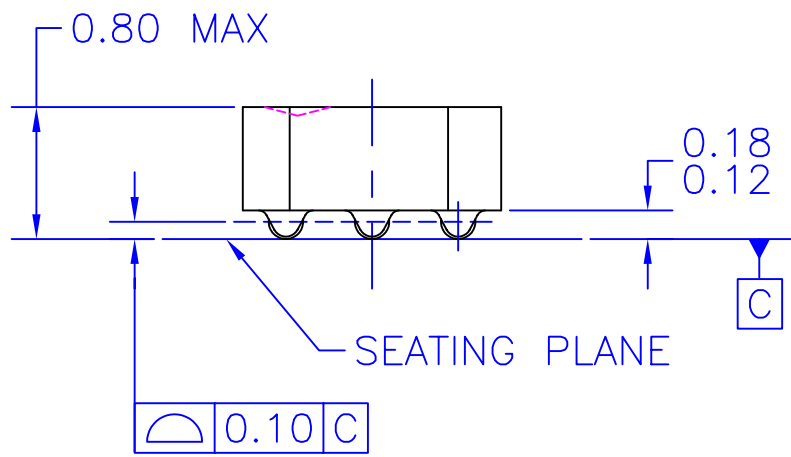
REVISIONS				
LTR	DESCRIPTION	E.C.N.	DATE	BY/APP'D
A	RELEASE TO DOCUMENT CONTROL	CB/071/02	20FEB2000	HTG
B	CHG BALL HEIGHT DIM FR 0.12 TO 0.18. ADD PKG CENTER LINE; REM DATUM C AT BALL POS GEOMETRIC TOL.	CB/116/02	12APR2002	HTG
C	CHANGE BALL POS TOL FR 0.10 TO 0.05	CB/343/02	21NOV2002	HTG
D	CHG PKG HOR BODY DIM TOL FR ±0.15 TO ±0.10; CHG DIM FR 1.50±0.08 TO 1.60-1.70; ADD PROTRUDING NUBS&DIM AT PKG EDGE	CB/259/03	14NOV2003	HTG
E	REMOVE GATE LABEL AT DRAIN PAD	CB/260/03	11DEC2003	HTG
F	CHG STUD DIM FR Ø0.20±0.02 TO (Ø0.25) REMOVE STUD POSITION TOLERANCE	CB/015/05	25JAN2005	HTG



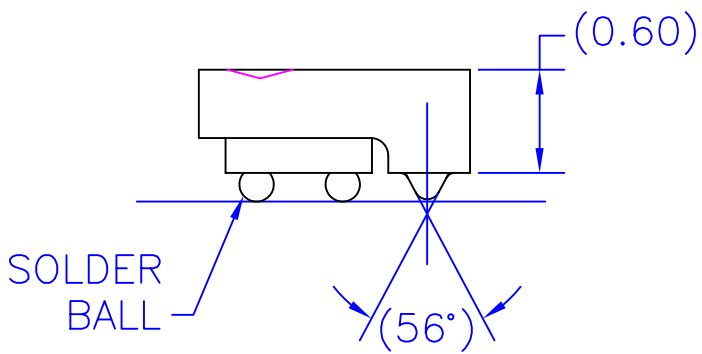
TOP VIEW



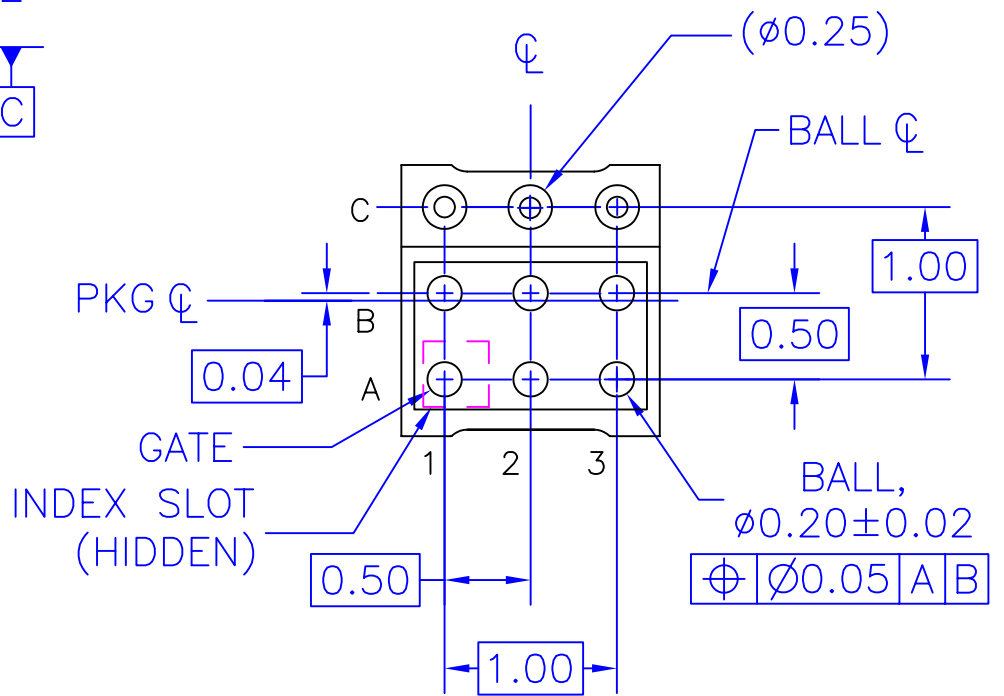
LAND PATTERN RECOMMENDATION



FRONT VIEW



SIDE VIEW



BOTTOM VIEW

NOTES: UNLESS OTHERWISE SPECIFIED

- A) ALL DIMENSIONS ARE IN MILLIMETERS.
- B) NO JEDEC REGISTRATION REFERENCE AS OF JULY 1999.
- C) BALL/STUD CONFIGURATION TABLE

TERMINAL ID	DESIGNATION	TERMINAL TYPE
C1,C2,C3	DRAIN	COPPER STUD
A1	GATE	BALL
A2,A3,B1,B2,B3	SOURCE	BALL

BGA06AREVF

APPROVALS	DATE	FAIRCHILD SEMICONDUCTOR™ CEBU PHILIPPINES			
DRAWN: J.P. GOMEZ	25JAN2005	6 BALL/3 STUD, MOSFET BGA, 1.5x1.5MM BODY, ATMLA			
CHECKED: H.T. GRANADA JR.					
APPROVED: M. GESTOLE					
G.S. BAJE					
		SCALE 25:1	SIZE A3	DRAWING NUMBER MKT-BGA06A	REV F
		FORMERLY: N/A	SHEET : 1 OF 1		